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<u>Fairchild Semiconductor</u> <u>NZT753</u>

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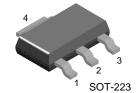




NZT753

PNP Current Driver Transistor

· This device is designed for power amplifier, regulator and switching circuits where speed is important. Sourced from Process 5P.



1. Base 2. Collector 3. Emitter

Absolute Maximum Ratings* T_A=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	- 100	V
V _{CBO}	Collector-Base Voltage	- 120	V
V _{EBO}	Emitter-Base Voltage	- 5.0	V
I _C	Collector Current - Continuous	- 4.0	Α
T _J , T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- NOTES:

 1) These ratings are based on a maximum junction temperature of 150°C.

 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics T_A=25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Max.	Units
Off Charac	teristics	•			
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = -10 \text{mA}, I_{B} = 0$	-100		V
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = -100\mu A, I_E = 0$	-120		V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = -100\mu A, I_C = 0$	-5.0		V
I _{CBO}	Collector-Base Cutoff Current	V _{CB} = -100V, I _E = 0 T _A = 100°C		-0.1 -10	μA μA
I _{EBO}	Emitter-Base Cutoff Current	$V_{EB} = -4V, I_C = 0$		-0.1	μΑ
On Charac	teristics *				
h _{FE}	DC Current Gain	V _{CE} = -2.0V, I _C = -50mA V _{CE} = -2.0V, I _C = -500mA V _{CE} = -2.0V, I _C = -1.0A	70 100 55	300	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	I _C = -1.0A, I _C = -50mA		-0.3	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	I _C = -1.0A, I _B = -100mA		-1.25	V
V _{BE} (on)	Base-Emitter On Voltage	$V_{CE} = -2.0V, I_{C} = -1.0A,$		-1.0	V
Small Sign	al Characteristics	·	•	•	•
f _T	Transition Frequency	$V_{CE} = -5V, I_{C} = -100 \text{mA}, f = 100 \text{MHz}$	75		MHz
Pulse Test: Pul	se Width ≤ 300μs, Duty Cycle ≤ 2.0%	•	4		

Thermal Characteristics * TA=25°C unless otherwise noted

Symbol	Parameter	Max.	Units	
P _D Total Device Dissipation		1.2	W	
5	Derate above 25C	9.7	mW/°C	
R _{e.IA}	Thermal Resistance, Junction to Ambient	103	°C/W	

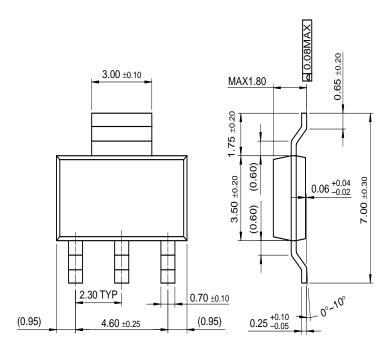
^{*} Device mounted on FR-4 PCB 36mm × 18mm × 1.5mm; mounting pad for the collector lead min 6cm².

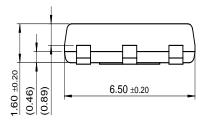




Package Dimensions

SOT-223





Dimensions in Millimeters

Distributor of Fairchild Semiconductor: Excellent Integrated System Limited Datasheet of NZT753 - TRANS PNP 100V 4A SOT-223

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